

General Description

The HTC721 (single), HTC722 (dual) and HTC724 (quad) are low noise, Low voltage and high slew rate operational amplifiers with an excellent bandwidth of 12MHz, a slew rate of 7 V/ μ s, and a quiescent current of 820 μ A per amplifier at 5V, the HTC72x family can be designed into a wide range of applications.

The HTC72x op-amps are designed to provide optimal performance in low voltage and low noise systems. The input common-mode voltage range includes ground, and the maximum input offset voltage are 4.0mV. These parts provide rail-to-rail output swing into heavy loads. The HTC72x family is specified for single or dual power supplies of +2.3V to +5.5V. All models are specified over the extended industrial temperature range of -40°C to +125°C.

The HTC721 is available in 5-lead SC70 and SOT-23 packages. The HTC722 is available in 8-lead MSOP and SOIC packages. The HTC724 is available in 14-lead TSSOP and SOIC packages.

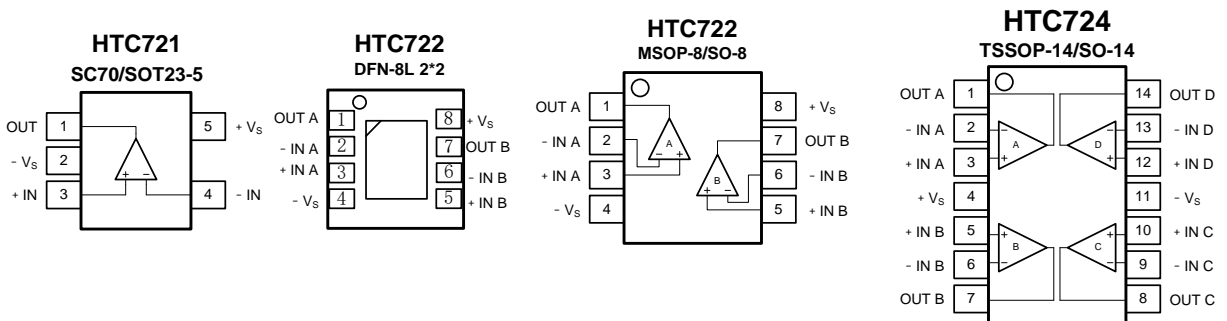
Features and Benefits

- High Slew Rate: 7 V/ μ s
- Wide Bandwidth: 12 MHz
- Low Power: 820 μ A per Amplifier Supply Current
- Settling Time to 0.1% with 2V Step: 0.26 μ s
- Overload Recovery Time: 0.31 μ s
- Low Noise : 45 nV/ \sqrt Hz
- High Gains of 110 dB for Active Filters and Gain Stages
- Low Offset Voltage: 4.2 mV Maximum
- Unit Gain Stable
- Rail-to-Rail Input and Output
 - Input Voltage Range: -0.2 to +5.2 V at 5V Supply
- Operating Power Supply: +2.3 V to +5.5 V
- Operating Temperature Range: -40°C to +125°C

Applications

- Photodiode Amplification
- Sensor Interfaces
- Audio Outputs
- Active Filters
- Driving A/D Converters
- Portable Equipment
- Battery-Powered Instrumentation

Pin Configurations (Top View)





Pin Description

Symbol	Description
-IN	Inverting Input of the Amplifier. The Voltage range can go from ($V_{S-} - 0.2V$) to ($V_{S+} + 0.2V$).
+IN	Non-Inverting Input of Amplifier. This pin has the same voltage range as -IN.
+V _S	Positive Power Supply. The voltage is from 2.3V to 5.5V. Split supplies are possible as long as the voltage between V _{S+} and V _{S-} is between 2.3V and 5.5V. A bypass capacitor of 0.1μF as close to the part as possible should be used between power supply pins or between supply pins and ground.
-V _S	Negative Power Supply. It is normally tied to ground. It can also be tied to a voltage other than ground as long as the voltage between V _{S+} and V _{S-} is from 2.3V to 5.5V. If it is not connected to ground, bypass it with a capacitor of 0.1μF as close to the part as possible.
OUT	Amplifier Output.
N/C	No Connection.

Ordering Information

Type Number	Package Name	Package Quantity	Marking Code
HTC721XC5/R6	SC70-5	Tape and Reel, 3 000	C71
HTC721XT5/R6	SOT23-5	Tape and Reel, 3 000	C71
HTC722XV8/R6	MSOP-8	Tape and Reel, 3 000	C72X
HTC722XS8/R8	SO-8	Tape and Reel, 4 000	C72X
HTC722XF8/R6	DFN-8L 2*2	Tape and Reel, 3 000	C72X
HTC724XT14/R6	TSSOP-14	Tape and Reel, 3 000	C74X
HTC724XS14/R5	SO-14	Tape and Reel, 2 500	C74X

Limiting Value

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Absolute Maximum Rating
Supply Voltage, V _{S+} to V _{S-}	7.0V
Common-Mode Input Voltage	V _{S-} - 0.5V to V _{S+} + 0.5V
Storage Temperature Range	-65°C to +150°C(T _J)
Junction Temperature	160°C
Lead Temperature Range (Soldering 10 sec)	260°C
Electrostatic Discharge Voltage	HBM ±4 000V
	MM ±400V

NOTE 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 2: Provided device does not exceed maximum junction temperature (T_J) at any time.

12MHz, High Slew Rate, RRIO CMOS Operational Amplifiers

Electrical Characteristics

$V_S = 5.0V$, $T_A = +25^\circ C$, $V_{CM} = V_S/2$, $V_O = V_S/2$, and $R_L = 10k\Omega$ connected to $V_S/2$, unless otherwise noted. **Boldface limits apply over the specified temperature range, $T_A = -40$ to $+125^\circ C$.**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
INPUT CHARACTERISTICS						
V_{OS}	Input offset voltage		-4.2	± 0.5	+4.2	mV
	over Temperature		-4.5		+4.5	
$V_{OS\ TC}$	Offset voltage drift	over Temperature		2		$\mu V/^\circ C$
I_B	Input bias current			1		pA
	over Temperature				800	
I_{OS}	Input offset current			1		pA
V_{CM}	Common-mode voltage range		$V_{S-}-0.2$		$V_{S+}+0.2$	V
CMRR	Common-mode rejection ratio	$V_{CM} = 0.05V$ to $3.0V$	80	94		dB
	over Temperature		70			
	over Temperature	$V_{CM} = V_{S-}-0.1$ to $V_{S+}+0.1 V$	60	75		
A_{VOL}	Open-loop voltage gain	$R_L = 10k\Omega$, $V_O = 0.05$ to $3.5 V$	98	108		dB
	over Temperature		86			
	over Temperature	$R_L = 600\Omega$, $V_O = 0.15$ to $3.5 V$	82	92		
			72			
R_{IN}	Input resistance		100			G Ω
C_{IN}	Input capacitance	Differential		2.0		pF
		Common mode		3.5		
OUTPUT CHARACTERISTICS						
V_{OH}	High output voltage swing	$R_L = 600\Omega$		$V_{S+}-100$		mV
		$R_L = 10k\Omega$		$V_{S+}-8$		
V_{OL}	Low output voltage swing	$R_L = 600\Omega$		70		mV
		$R_L = 10k\Omega$		6		
Z_{OUT}	Closed-loop output impedance	$f = 200kHz$, $G = +1$		0.4		Ω
	Open-loop output impedance	$f = 1MHz$, $I_O = 0$		2.6		
I_{SC}	Short-circuit current	Source current through 10Ω		55		mA
		Sink current through 10Ω		50		
DYNAMIC PERFORMANCE						
GBW	Gain bandwidth product	$f = 1kHz$		12		MHz
Φ_M	Phase margin	$C_L = 100pF$		66		$^\circ$
SR	Slew rate	$G = +1$, $C_L = 100pF$, $V_O = 1.5V$ to $3.5V$		7		V/ μs
BW _P	Full power bandwidth	<1% distortion		400		kHz
t_S	Settling time	To 0.1%, $G = +1$, 2V step		0.26		μs
		To 0.01%, $G = +1$, 2V step		0.28		



12MHz, High Slew Rate, RRIO CMOS Operational Amplifiers

Electrical Characteristics (continued)

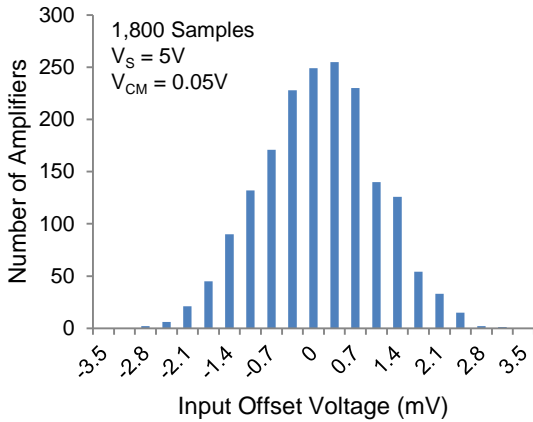
$V_S = 5.0V$, $T_A = +25^\circ C$, $V_{CM} = V_S/2$, $V_O = V_S/2$, and $R_L = 10k\Omega$ connected to $V_S/2$, unless otherwise noted. **Boldface limits apply over the specified temperature range, $T_A = -40$ to $+125^\circ C$.**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t_{OR}	Overload recovery time	$V_{IN} * Gain > V_S$		0.31		μs
THD+N	Total harmonic distortion + noise	$f = 1kHz, G = +1, V_O = 3V_{pp}$		0.0013		%
NOISE PERFORMANCE						
V_n	Input voltage noise	$f = 0.1$ to 10 Hz		8		μV_{P-P}
e_n	Input voltage noise density	$f = 10kHz$		45		nV/\sqrt{Hz}
POWER SUPPLY						
V_S	Operating supply voltage		2.3		5.5	V
PSRR	Power supply rejection ratio	$V_S = 2.7V$ to $5.5V, V_{CM} < V_{St} - 2V$	82	98		dB
	over Temperature		75			
I_Q	Quiescent current (per amplifier)			820	1050	μA
	over Temperature				1250	
THERMAL CHARACTERISTICS						
T_A	Operating temperature range		-40		+125	$^\circ C$
θ_{JA}	Package Thermal Resistance	SC70-5		333		$^\circ C/W$
		SOT23-5		190		
		MSOP-8		216		
		SO-8		125		
		TSSOP-14		112		
		SO-14		115		

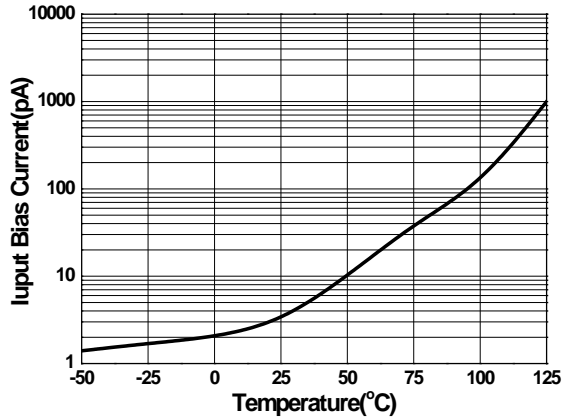
12MHz, High Slew Rate, RRIO CMOS Operational Amplifiers

Typical Performance Characteristics

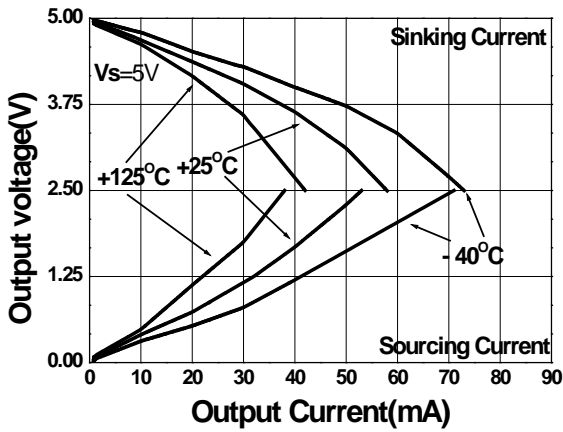
At $T_A = +25^\circ\text{C}$, $V_{CM} = V_S/2$, and $R_L = 10\text{k}\Omega$ connected to $V_S/2$, unless otherwise noted.



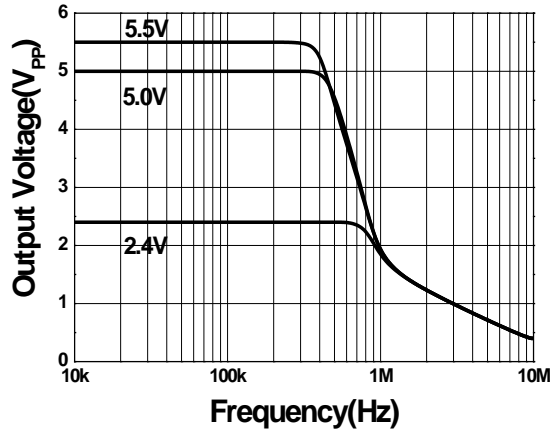
Input Offset Voltage Production Distribution.



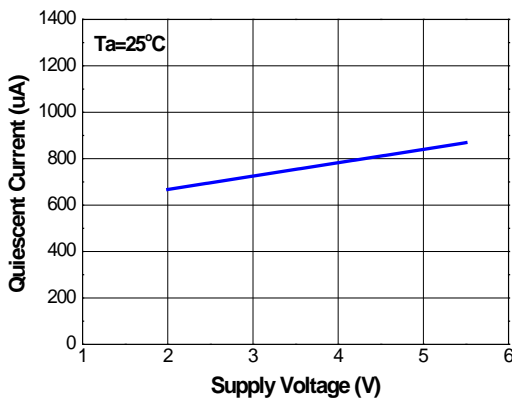
Input Bias Current as a function of Temperature.



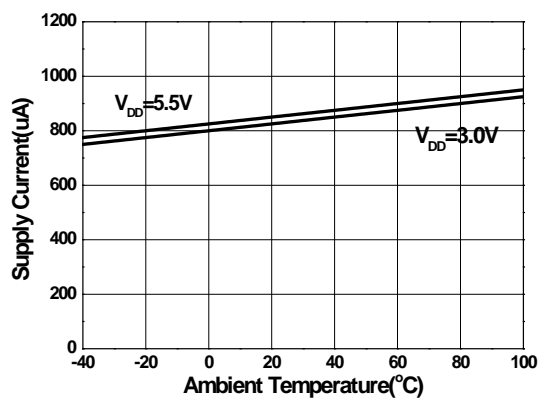
Output Voltage Swing as a function of Output Current.



Maximum Output Voltage as a function of Frequency.



Quiescent Current as a function of Supply Voltage.



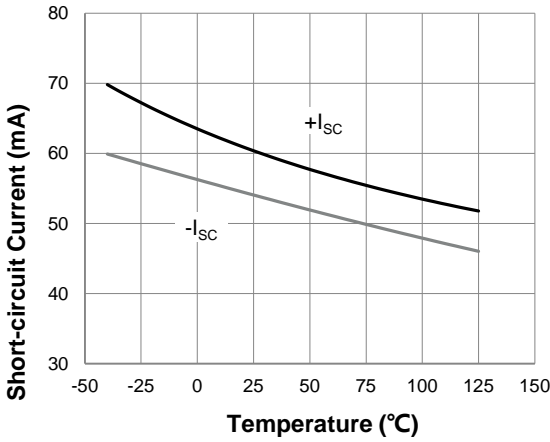
Quiescent Current as a function of Temperature.



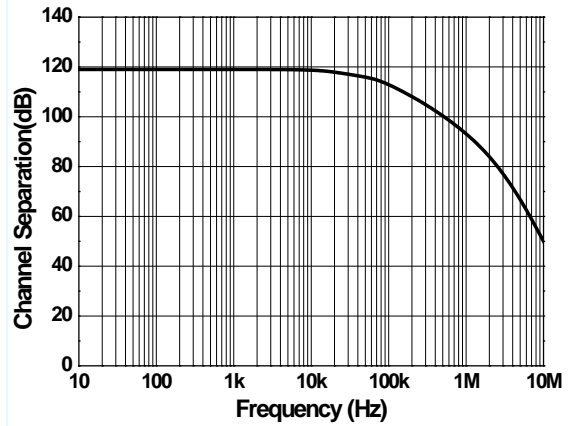
12MHz, High Slew Rate, RRIO CMOS Operational Amplifiers

Typical Performance Characteristics (continued)

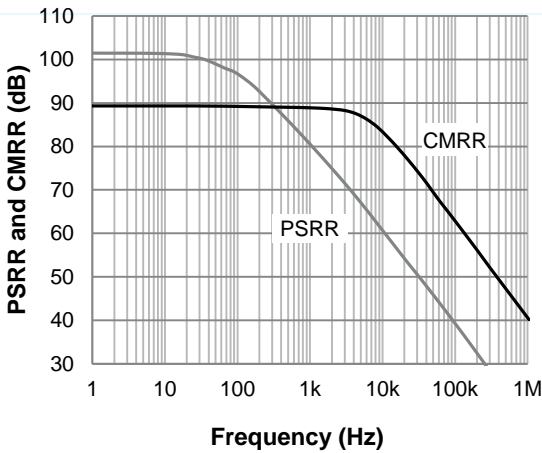
At $T_A = +25^\circ\text{C}$, $V_{CM} = V_S/2$, and $R_L = 10\text{k}\Omega$ connected to $V_S/2$, unless otherwise noted.



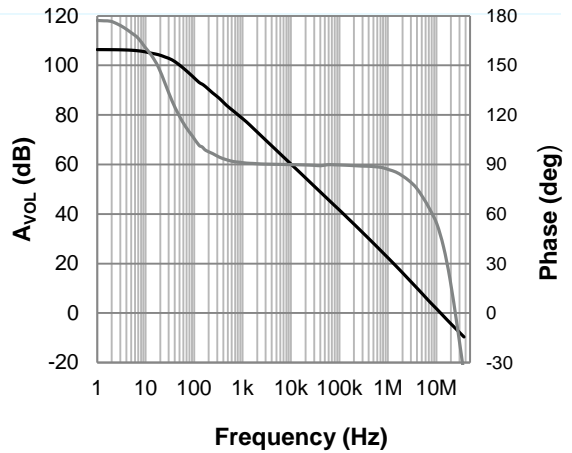
Short-circuit Current as a function of Temperature.



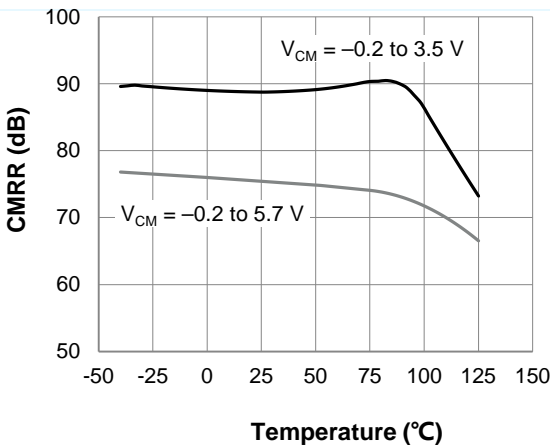
Channel Separation as a function of Frequency.



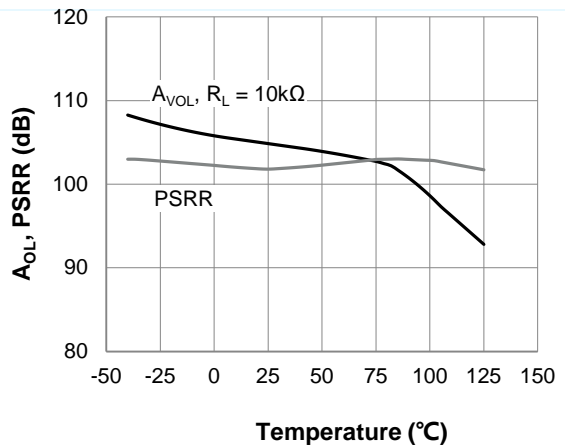
Power Supply and Common-mode Rejection Ratio as a function of Frequency.



Open-loop Gain and Phase as a function of Frequency.



Common-mode Rejection Ratio as a function of Temperature.

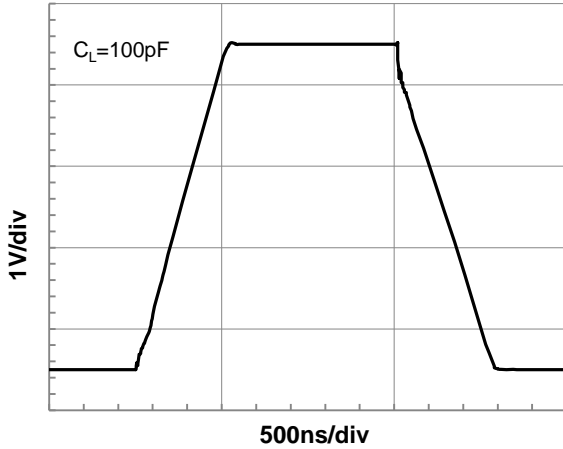


Open-loop Gain and Power Supply Rejection Ratio as a function of Temperature.

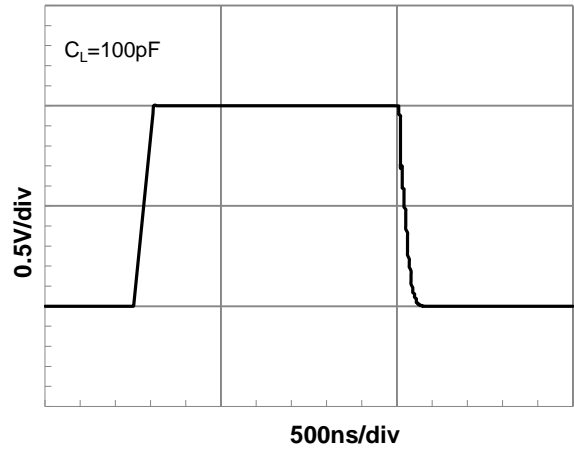
12MHz, High Slew Rate, RRIO CMOS Operational Amplifiers

Typical Performance Characteristics (continued)

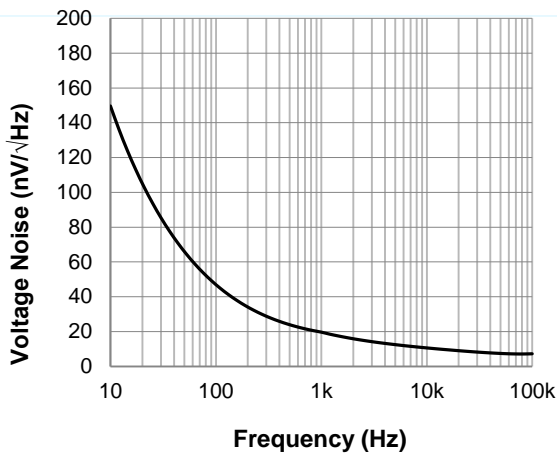
At $T_A = +25^\circ\text{C}$, $V_{CM} = V_S/2$, and $R_L = 10\text{k}\Omega$ connected to $V_S/2$, unless otherwise noted.



Large Signal Step Response.



Small Signal Step Response.



Input Voltage Noise Spectral Density as a function of Frequency.



Application Notes

LOW INPUT BIAS CURRENT

The HTC72x family is a CMOS op-amp family and features very low input bias current in pA range. The low input bias current allows the amplifiers to be used in applications with high resistance sources. Care must be taken to minimize PCB Surface Leakage. See below section on “PCB Surface Leakage” for more details.

PCB SURFACE LEAKAGE

In applications where low input bias current is critical, Printed Circuit Board (PCB) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low humidity conditions, a typical resistance between nearby traces is $10^{12}\Omega$. A 5V difference would cause 5pA of current to flow, which is greater than the HTC72x’s input bias current at +25°C ($\pm 1\text{fA}$, typical). It is recommended to use multi-layer PCB layout and route the op-amp’s -IN and +IN signal under the PCB surface.

The effective way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 1 for Inverting Gain application.

- For Non-Inverting Gain and Unity-Gain Buffer:
 - Connect the non-inverting pin (+IN) to the input with a wire that does not touch the PCB surface.
 - Connect the guard ring to the inverting input pin (-IN). This biases the guard ring to the Common Mode input voltage.
- For Inverting Gain and Trans-impedance Gain Amplifiers (convert current to voltage, such as photo detectors):
 - Connect the guard ring to the non-inverting input pin (+IN). This biases the guard ring to the same reference voltage as the op-amp (e.g., $V_S/2$ or ground).
 - Connect the inverting pin (-IN) to the input with a wire that does not touch the PCB surface.

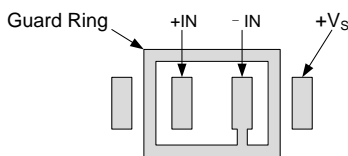


Figure 1. Use a guard ring around sensitive pins

GROUND SENSING AND RAIL TO RAIL

The input common-mode voltage range of the HTC72x series extends 300mV beyond the supply rails. This is achieved with a complementary input stage—an N-channel input differential pair in parallel with a P-channel differential pair. For normal operation, inputs should be limited to this range. The absolute maximum input voltage is 500mV beyond the supplies. Inputs greater than the input common-mode range but less than the maximum input voltage, while not valid, will not cause any damage to the op-amp. Unlike some other op-amps, if input current is limited, the inputs may go beyond the supplies without phase inversion, as shown in Figure 2. Since the input common-mode range extends from $(V_{S-} - 0.3\text{V})$ to $(V_{S+} + 0.3\text{V})$, the HTC72x op-amps can easily perform ‘true ground’ sensing.

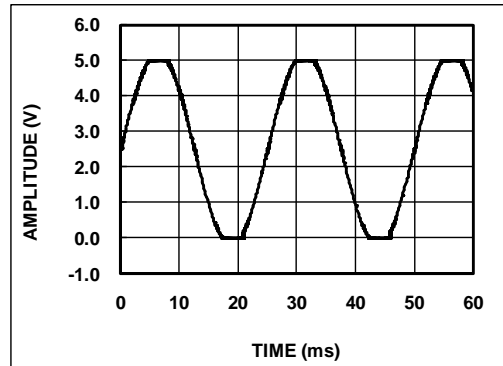


Figure 2. No Phase Inversion with Inputs Greater Than the Power-Supply Voltage

A topology of class AB output stage with common-source transistors is used to achieve rail-to-rail output. For light resistive loads (e.g. 100kΩ), the output voltage can typically swing to within 5mV from the supply rails. With moderate resistive loads (e.g. 10kΩ), the output can typically swing to within 10mV from the supply rails and maintain high open-loop gain. See the Typical Characteristic curve, Output Voltage Swing as a function of Output Current, for more information.

The maximum output current is a function of total supply voltage. As the supply voltage to the amplifier increases, the output current capability also increases. Attention must be paid to keep the junction temperature of the IC below 150°C when the output is in continuous short-circuit. The output of the amplifier has reverse-biased ESD diodes connected to each supply. The output should not be forced more than 0.5V beyond either supply, otherwise current will flow through these diodes.

CAPACITIVE LOAD AND STABILITY

The HTC72x can directly drive 1nF in unity-gain without oscillation. The unity-gain follower (buffer) is the most sensitive configuration to capacitive loading. Direct capacitive loading reduces the phase margin of amplifiers and this results in ringing or even oscillation. Applications that require greater capacitive drive capability should use an isolation resistor between the output and the capacitive load like the circuit in Figure 3. The isolation resistor R_{ISO} and the load capacitor C_L form a zero to increase stability. The bigger the R_{ISO} resistor value, the more stable V_{OUT} will be. Note that this method results in a loss of gain accuracy because R_{ISO} forms a voltage divider with the R_L .

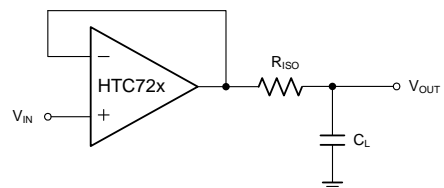


Figure 3. Indirectly Driving Heavy Capacitive Load

An improvement circuit is shown in Figure 4. It provides DC accuracy as well as AC stability. The R_F provides the DC accuracy by connecting the inverting signal with the output.

Application Notes (continued)

The C_F and R_{ISO} serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving phase margin in the overall feedback loop.

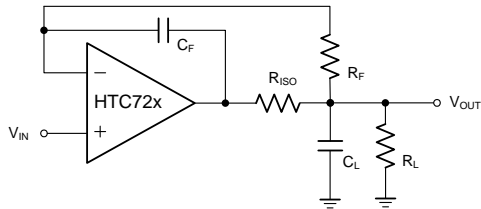


Figure 4. Indirectly Driving Heavy Capacitive Load with DC Accuracy

For no-buffer configuration, there are two other ways to increase the phase margin: (a) by increasing the amplifier's gain, or (b) by placing a capacitor in parallel with the feedback resistor to counteract the parasitic capacitance associated with inverting node.

POWER SUPPLY LAYOUT AND BYPASS

The HTC72x family operates from either a single +2.3V to +5.5V supply or dual $\pm 1.15V$ to $\pm 3.00V$ supplies. For single-supply operation, bypass the power supply V_S with a ceramic capacitor (i.e. 0.01 μF to 0.1 μF) which should be placed close (within 2mm for good high frequency

performance) to the V_S pin. For dual-supply operation, both the V_{S+} and the V_{S-} supplies should be bypassed to ground with separate 0.1 μF ceramic capacitors. A bulk capacitor (i.e. 2.2 μF or larger tantalum capacitor) within 100mm to provide large, slow currents and better performance. This bulk capacitor can be shared with other analog parts.

Good PC board layout techniques optimize performance by decreasing the amount of stray capacitance at the op-amp's inputs and output. To decrease stray capacitance, minimize trace lengths and widths by placing external components as close to the device as possible. Use surface-mount components whenever possible. For the op-amp, soldering the part to the board directly is strongly recommended. Try to keep the high frequency big current loop area small to minimize the EMI (electromagnetic interfacing).

GROUNDING

A ground plane layer is important for the HTC72x circuit design. The length of the current path speed currents in an inductive ground return will create an unwanted voltage noise. Broad ground plane areas will reduce the parasitic inductance.

INPUT-TO-OUTPUT COUPLING

To minimize capacitive coupling, the input and output signal traces should not be parallel. This helps reduce unwanted positive feedback.

Typical Application Circuits

DIFFERENTIAL AMPLIFIER

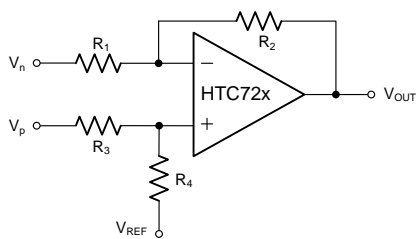
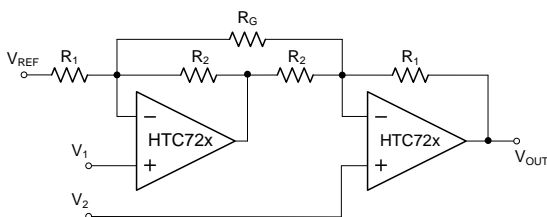


Figure 5. Differential Amplifier

The circuit shown in Figure 5 performs the difference function. If the resistors ratios are equal $R_4/R_3 = R_2/R_1$, then:

$$V_{OUT} = (V_p - V_n) \times R_2/R_1 + V_{REF}$$

INSTRUMENTATION AMPLIFIER

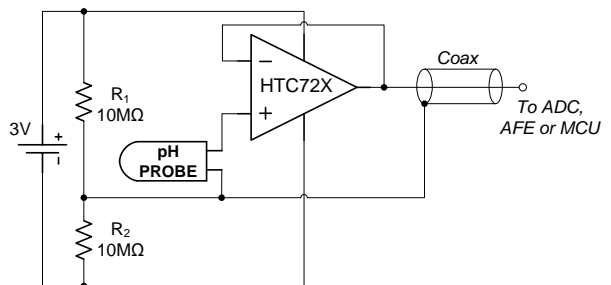


$$V_{OUT} = (V_1 - V_2) \left(1 + \frac{R_1}{R_2} + \frac{2R_1}{R_G} \right) + V_{REF}$$

Figure 6. Instrumentation Amplifier

The HTC72x family is well suited for conditioning sensor signals in battery-powered applications. Figure 6 shows a two op-amp instrumentation amplifier, using the HTC72x op-amps. The circuit works well for applications requiring rejection of common-mode noise at higher gains. The reference voltage (V_{REF}) is supplied by a low-impedance source. In single voltage supply applications, the V_{REF} is typically $V_S/2$.

BUFFERED CHEMICAL SENSORS



All components contained within the pH probe

Figure 7. Buffered pH Probe

The HTC72x family has input bias current in the pA range. This is ideal in buffering high impedance chemical sensors, such as pH probes. As an example, the circuit in Figure 7 eliminates expansive low-leakage cables that is required to connect a pH probe (general purpose combination pH probes, e.g Corning 476540) to metering ICs such as ADC, AFE and/or MCU. An HTC72x op-amp

Typical Application Circuits (continued)

and a lithium battery are housed in the probe assembly. A conventional low-cost coaxial cable can be used to carry the op-amp's output signal to subsequent ICs for pH reading.

SHUNT-BASED CURRENT SENSING AMPLIFIER

The current sensing amplification shown in Figure 8 has a slew rate of $2\pi fV_{PP}$ for the output of sine wave signal, and has a slew rate of $2fV_{PP}$ for the output of triangular wave signal. In most of motor control systems, the PWM frequency is at 10kHz to 20kHz, and one cycle time is $100\mu s$ for a 10kHz of PWM frequency. In current shunt monitoring for a motor phase, the phase current is converted to a phase voltage signal for ADC sampling. This sampling voltage signal must be settled before entering the ADC. As the Figure 8 shown, the total settling time of a current shunt monitor circuit includes: the rising edge delay time (t_{SR}) due to the op-amp's slew rate, and the measurement settling time (t_{SET}). If the minimum duty cycle of the PWM is defined at 5%, and the t_{SR} is required at 20% of a total time window for a phase current monitoring, in case of a 3.3V motor control system (3.3V MCU with 12-bit ADC), the op-amp's slew rate should be more than:

$$3.3V / (100\mu s \times 5\% \times 20\%) = 3.3 V/\mu s$$

At the same time, the op-amp's bandwidth should be much greater than the PWM frequency, like 10 times at least.

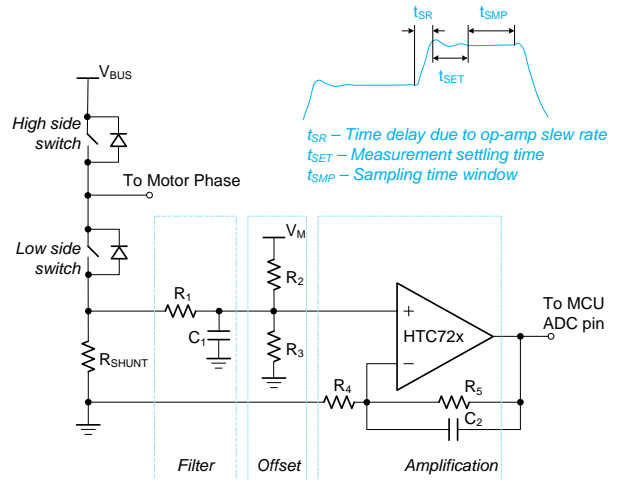
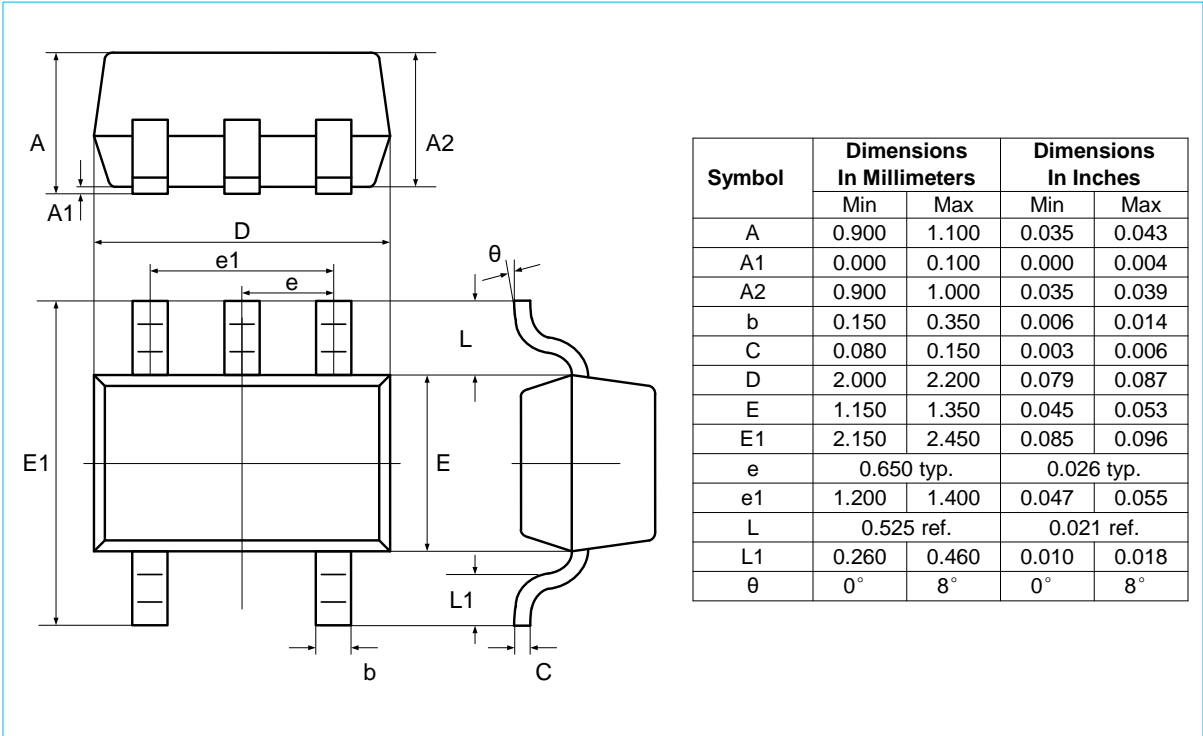


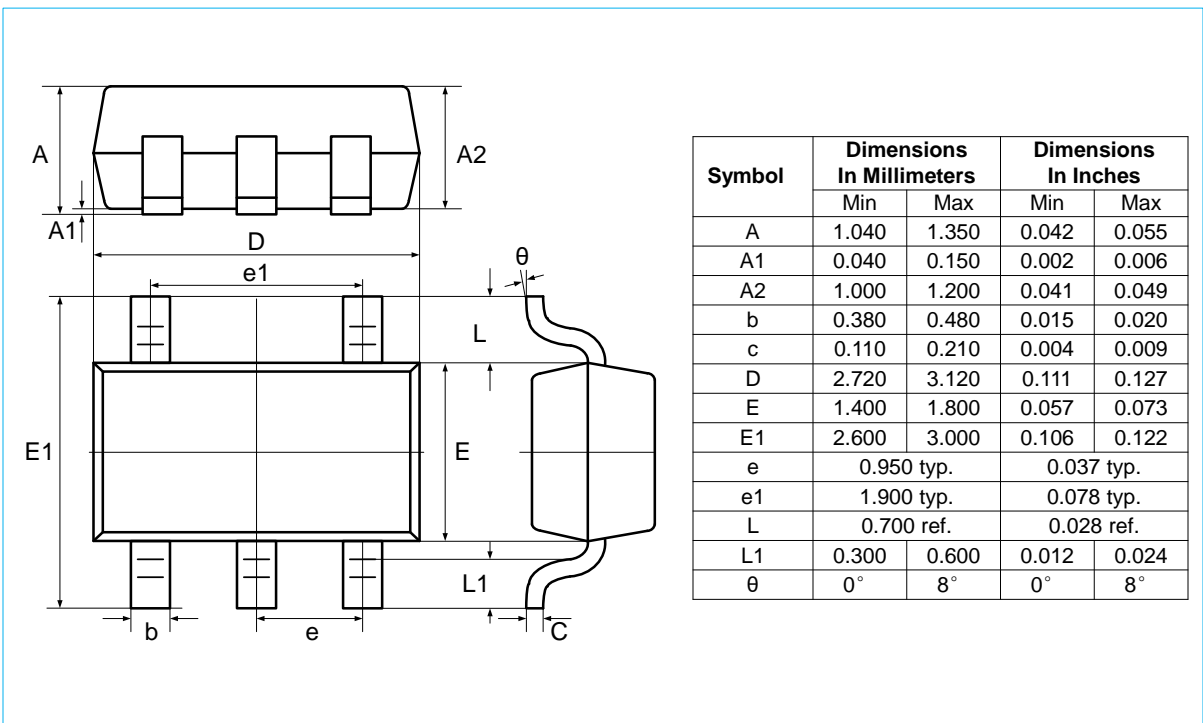
Figure 8. Current Shunt Monitor Circuit

Package Outlines

SC70-5 (SOT353)



SOT23-5



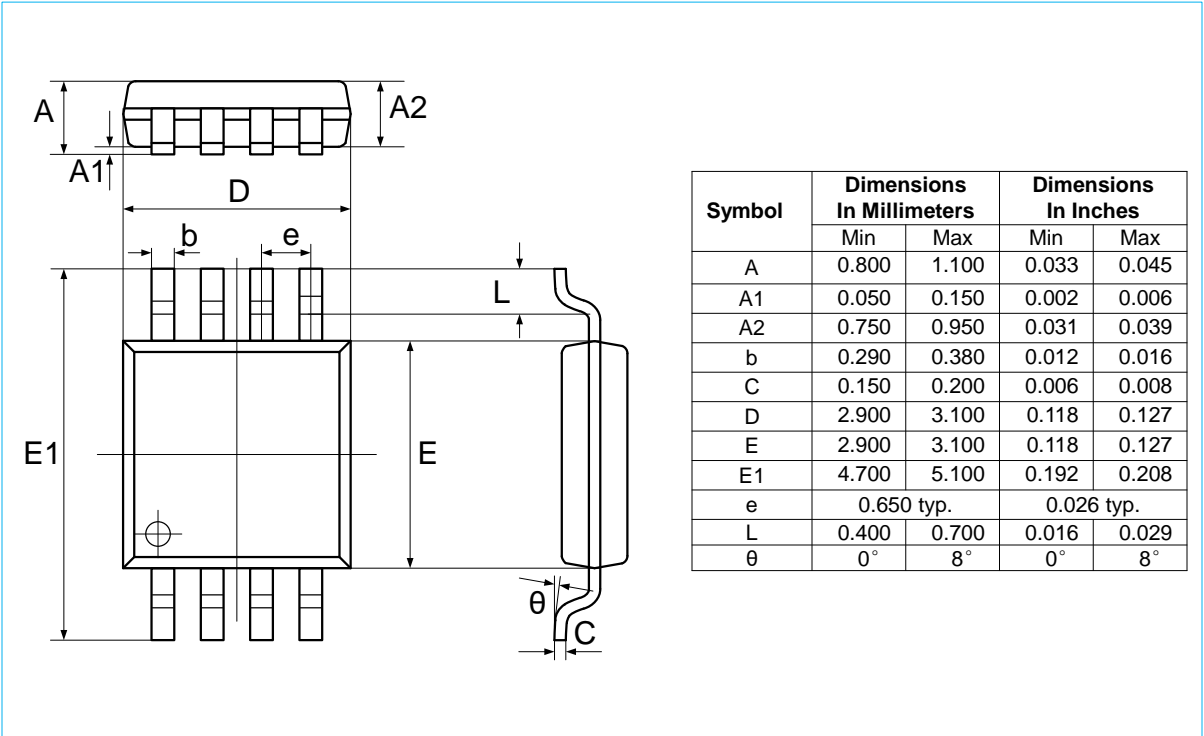


HTC721, HTC722, HTC724

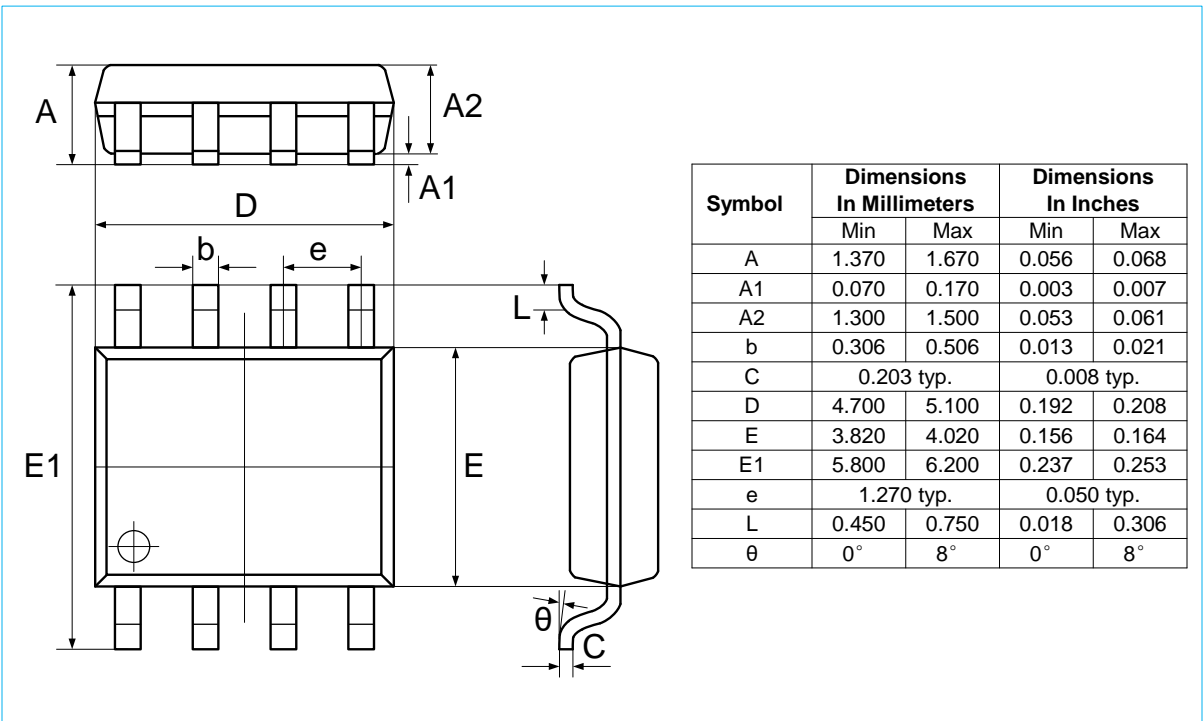
12MHz, High Slew Rate, RRIO CMOS Operational Amplifiers

Package Outlines (continued)

MSOP-8



SO-8



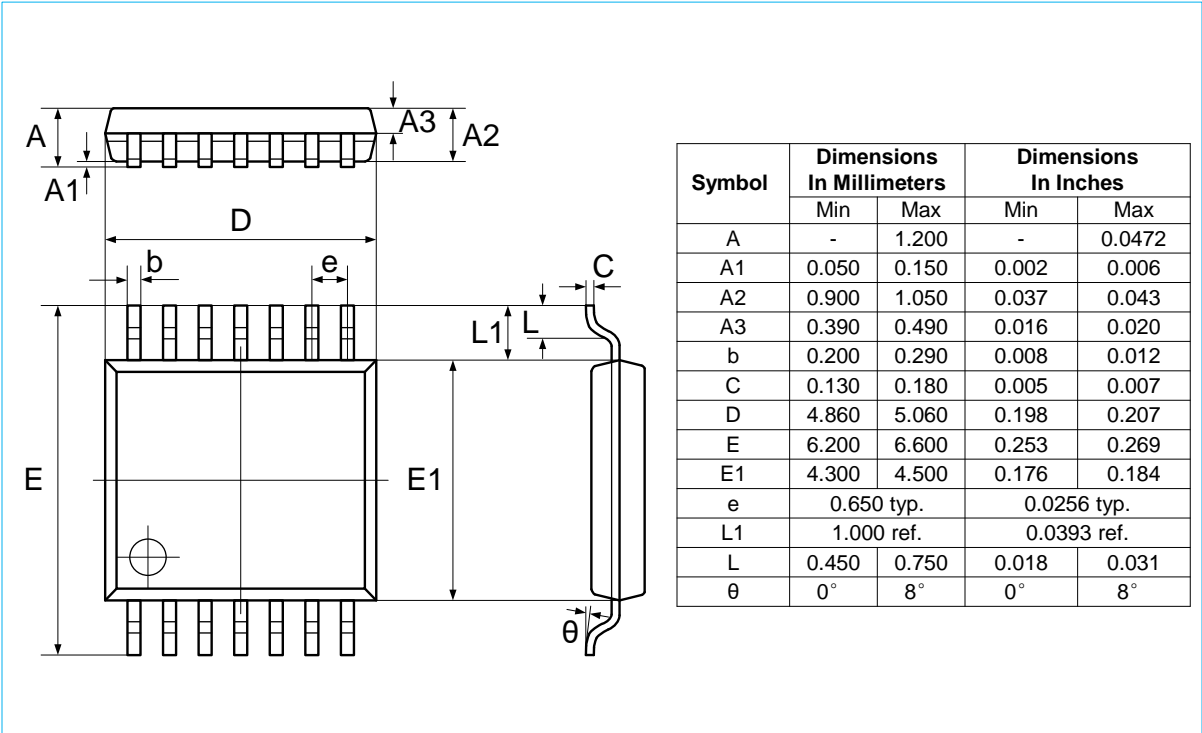
HTC721, HTC722, HTC724



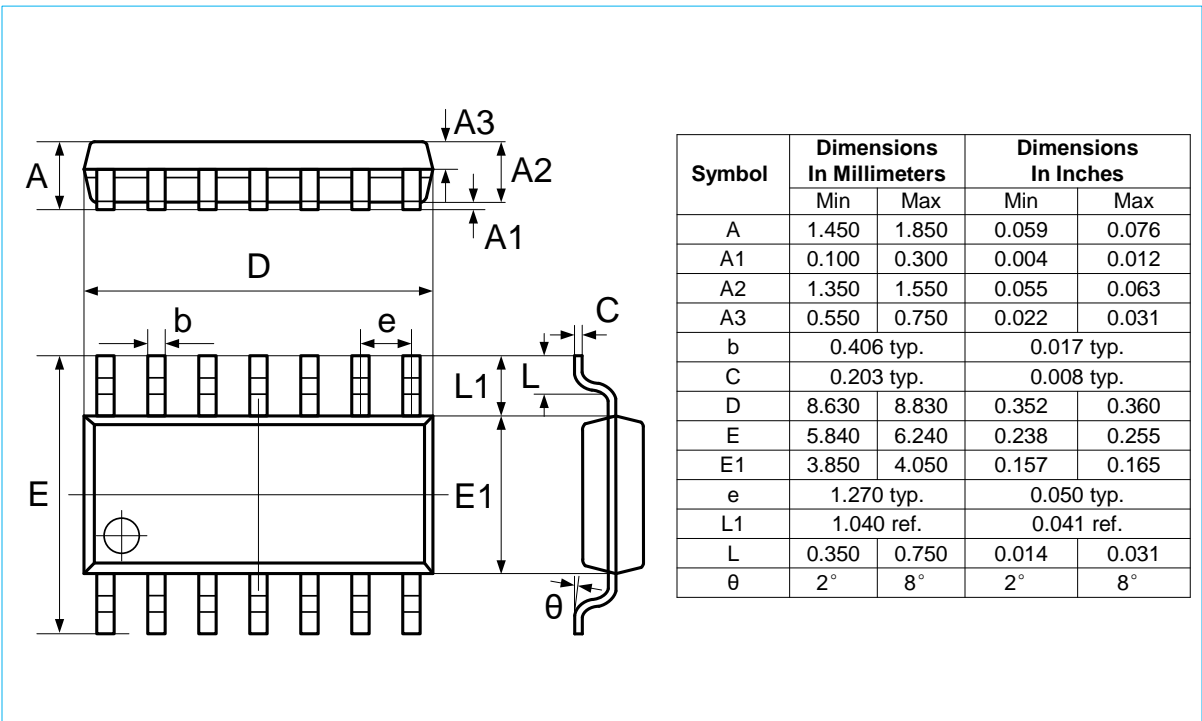
12MHz, High Slew Rate, RRIO CMOS Operational Amplifiers

Package Outlines (continued)

TSSOP-14



SO-14





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